

TENTATIVE

TOSHIBA Photocoupler GaAlAs IRed & Photo-Triac

TLP168J

Triac Drive
Programmable Controllers
AC-Output Module
Solid State Relay

The TOSHIBA mini flat coupler TLP168J is a small outline coupler, suitable for surface mount assembly.

The TLP168J consists of a photo triac, optically coupled to a GaA ℓ As infrared emitting diode.

• Zero-voltage crossing turn-on

• Peak off-state voltage: 600 V (min.)

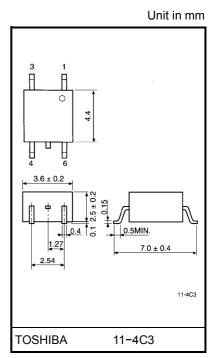
• Trigger LED current: 3 mA (max.)

• On-state current: 70 mA (max.)

• Isolation voltage: 2500 Vrms (min.)

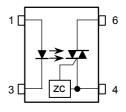
Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
	Forward current		I _F	20	mA	
	Forward current derating (Ta ≥ 25°C)		ΔI _F / °C	-0.2	mA / °C	
LED	Peak forward current (100µs pulse, 100 pps)		I _{FP}	1	Α	
	Reverse voltage	V _R	5	V		
	Junction temperature		Tj	125	°C	
	Off– state output terminal voltage		V _{DRM}	600	V	
	On-state RMS current	Ta=25°C	l=	70	mA	
		Ta=70°C	I _{T(RMS)}	40		
Detector	On–state current derating (Ta ≥ 25°C)		ΔI _T / °C	-0.67	mA / °C	
De	Peak on–state current (100µs pulse, 120 pps)		I _{TP}	2	Α	
	Peak nonrepetitive surge current (PW=10ms, DC=10%)		I _{TSM}	1.2	Α	
	Junction temperature		Tj	115	°C	
Stora	rage temperature range		T _{stg}	-55~125	°C	
Opei	Operating temperature range		T _{opr}	-40 ~ 100	°C	
Lead	I soldering temperature (10s)		T _{sol}	260	°C	
	Isolation voltage (AC, 1 min., R.H. ≤ 60%)		BVS	2500	Vrms	



Weight: 0.09 g

Pin Configurations



- 1: Anode
- 3: Cathode
- 4: Terminal 1
- 6: Terminal 2

(Note) Device considered a two terminal device: Pins 1 and 3 shorted together and pins 4 and 6 shorted together.

TLP168J

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	_	_	240	V _{ac}
Forward current	l _F	4.5	6	7.5	mA
Peak on-state current	I _{TP}	_	_	1	Α
Operating temperature	T _{opr}	-10	_	85	°C

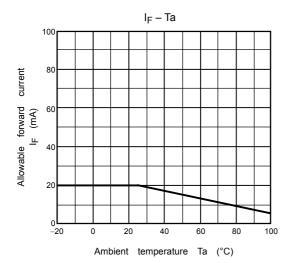
Individual Electrical Characteristics (Ta = 25°C)

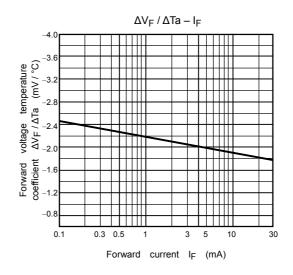
Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	V _F	I _F =10mA	1.2	1.4	1.7	V
	Reverse current	I _R	V _R =3V	_	_	10	μA
	Capacitance	C _T	V=0, f=1MHz	_	30	_	pF
Detector	Peak off-state current	I _{DRM}	V _{DRM} =600V	_	10	1000	nA
	Peak on-state voltage	V_{TM}	I _{TM} =70mA	_	1.7	2.8	V
	Holding current	lΗ	_	_	0.6	_	mA
	Critical rate of rise of off– state voltage	dv / dt	V _{in} =240Vrms, Ta=85°C	200	500	_	V / µs
	Critical rate of rise of commutating voltage	dv / dt(c)	V _{in} =60Vrms I _T =15mArms	_	0.2	_	V / µs

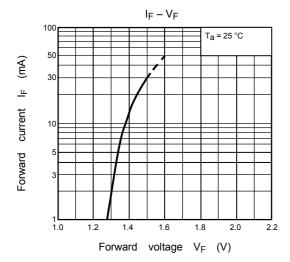
Coupled Electrical Characteristics (Ta = 25°C)

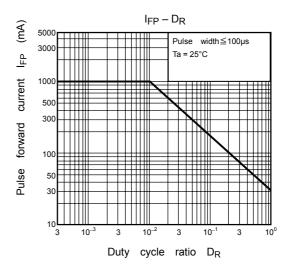
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Trigger LED current	I _{FT}	V _T =6V	_	_	3	mA	
Inhibit voltage	V _{IH}	I _F =Rated I _{FT}	1	1	50	V	
Leakage in inhibited state	ΙΗ	I _F =Rated I _{FT} V _T = Rated V _{DRM}		200	600	μΑ	
Capacitance (input to output)	Cs	V _S =0, f=1MHz	_	0.8	_	pF	
Isolation resistance	R _S	V _S =500V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	_	Ω	
	BVS	AC, 1 minute	2500	_	_	Vrms	
Isolation voltage		AC, 1 second, in oil	_	5000	_	VIIIIS	
		DC, 1 minute, in oil	_	5000	_	Vdc	

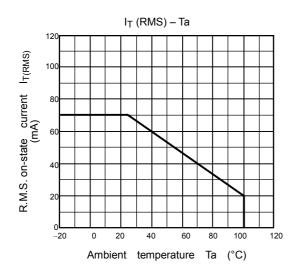
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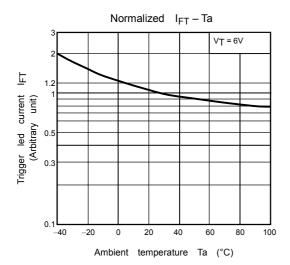


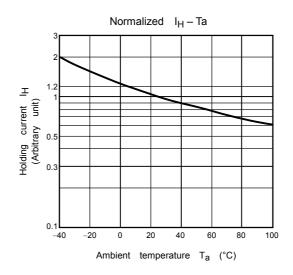


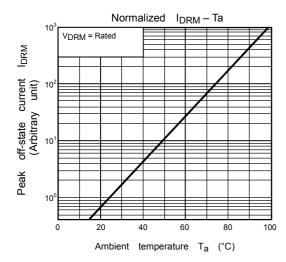


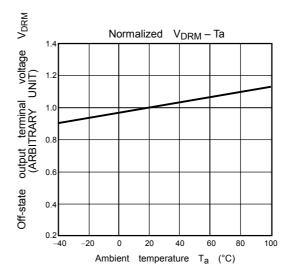


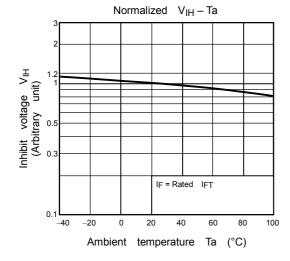
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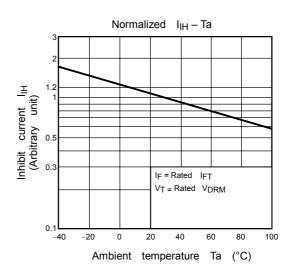












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